

IN THE CLAIMS:

Please amend claims 1, 2, 3, 59, 60, and 68.

1. (Currently amended) A process for preparing a silicon melt in a crucible from which a single crystal silicon ingot is grown for use in growing the single crystal silicon ingot by the Czochralski method, the process comprising:

a. forming a partially melted charge in the crucible, the partially melted charge comprising molten silicon and unmelted polycrystalline silicon, the molten silicon having an upper surface, the unmelted polycrystalline silicon comprising an exposed portion that is above the upper surface of the molten silicon;

b. rotating the crucible from which the single crystal silicon ingot is grown;

c. feeding additional polycrystalline silicon into the rotating crucible by intermittently delivering the additional polycrystalline silicon out of a feed tube in the crucible and onto the exposed portion of the unmelted polycrystalline silicon of said partially melted charge in the crucible from which the single crystal silicon ingot is grown, the intermittent delivery comprising a plurality of alternating on-periods and off-periods, wherein each on-period comprises flowing the additional polycrystalline silicon through a feed device that directs the flow of the additional polycrystalline silicon onto the unmelted polycrystalline silicon of the partially melted charge in the crucible for an on-duration, and each off-period comprises interrupting the flow of the additional polycrystalline silicon for an off-duration; and

d. melting the unmelted polycrystalline silicon and the additional polycrystalline silicon to form the silicon melt in the crucible from which the single crystal silicon ingot is grown.

2. (Currently amended) A process for preparing a silicon melt in a crucible from which a single crystal silicon ingot is grown for use in growing the single crystal silicon ingot by the Czochralski method, the process comprising:

- a. loading the crucible with polycrystalline silicon;
- b. rotating the loaded crucible from which the single crystal silicon ingot is grown;
- c. heating the loaded polycrystalline silicon to form molten silicon and unmelted polycrystalline silicon, the molten silicon comprising an upper surface, the unmelted polycrystalline silicon comprising an exposed portion that is above the upper surface of the molten silicon;
- d. feeding additional polycrystalline silicon into the rotating crucible by intermittently delivering the additional polycrystalline silicon out of a feed tube in the crucible and onto the exposed portion of the unmelted polycrystalline silicon of said partially melted charge in the crucible from which the single crystal silicon ingot is grown, the intermittent delivery comprising a plurality of alternating on-periods and off-periods, wherein each on-period comprises flowing the additional polycrystalline silicon through a feed device that directs the flow of the additional polycrystalline silicon onto the unmelted polycrystalline silicon for an on-duration, and each off-period comprises interrupting the flow of the additional polycrystalline silicon for an off-duration; and
- e. melting the loaded polycrystalline silicon and the additional polycrystalline silicon to form the silicon melt in the crucible from which the single crystal silicon ingot is grown.

3. (Currently amended) A process for preparing a silicon melt in a crucible from which a single crystal silicon ingot is

grown for use in growing the single crystal silicon ingot by the Czochralski method, the process comprising:

a. loading the crucible with polycrystalline silicon, the crucible comprising an interior wall and having an inner diameter, D ;

b. rotating the loaded crucible from which the single crystal silicon ingot is grown at a rate, r ;

c. heating the loaded polycrystalline silicon to form molten silicon and unmelted polycrystalline silicon, the molten silicon comprising an upper surface, the unmelted polycrystalline silicon comprising an exposed portion that is above the upper surface of the molten silicon, the exposed unmelted polycrystalline having a center and a width, d , that corresponds to the longest distance between two points along the interface between the exposed unmelted polycrystalline silicon and the upper surface of the molten silicon wherein the center of the exposed unmelted polycrystalline is above the interface between the exposed unmelted polycrystalline silicon and the upper surface of the molten silicon;

d. feeding additional polycrystalline silicon into the rotating crucible by intermittently delivering the additional polycrystalline silicon at a feed rate, F , out of a feed tube in the crucible and onto the exposed portion of the unmelted polycrystalline silicon of said partially melted charge in the crucible from which the single crystal silicon ingot is grown, thereby maintaining the width of the exposed unmelted polycrystalline silicon, d , the intermittent delivery comprising a plurality of alternating on-periods and off-periods, wherein each on-period comprises flowing the additional polycrystalline silicon at a flow rate, f , for a duration, t_{on} , through a feed device that directs the additional polycrystalline silicon onto the exposed unmelted polycrystalline silicon, and wherein each off-period comprises interrupting the flow of the additional

polycrystalline silicon through the feed device for a duration, t_{off} ; and

e. melting the loaded polycrystalline silicon and the additional polycrystalline silicon to form the silicon melt in the crucible from which the single crystal silicon ingot is grown.

4. (Original) The process as set forth in claim 3 wherein the interface between the unmelted polycrystalline silicon and the upper surface of the molten silicon is approximately equidistant from the center of the unmelted polycrystalline silicon.

5. (Original) The process as set forth in claim 4 wherein the interface between unmelted polycrystalline silicon and the upper surface of the molten silicon is approximately equidistant from the interior wall of the crucible.

6. (Previously presented) The process as set forth in claim 5 wherein the polycrystalline silicon that is loaded into the crucible is chunk polycrystalline silicon and the additional polycrystalline silicon fed into the crucible is granular polycrystalline silicon.

7. (Original) The process as set forth in claim 6 wherein the loaded chunk polycrystalline silicon comprises about 40% to about 65% by weight of the silicon melt.

8. (Original) The process as set forth in claim 6 wherein the loaded chunk polycrystalline silicon comprises about 50% to about 60% by weight of the silicon melt.

9. (Original) The process as set forth in claim 6 wherein d ranges from about 65% to about 85% of D .

10. (Original) The process as set forth in claim 6 wherein d is about 75% of D .

11. (Original) The process as set forth in claim 6 wherein r is at least about 1 rpm.

12. (Original) The process as set forth in claim 6 wherein r ranges from about 1 rpm to about 5 rpm.

13. (Original) The process as set forth in claim 6 wherein r ranges from about 2 rpm to about 3 rpm.

14. (Original) The process as set forth in claim 6 wherein r is about 2.1 rpm.

15. (Original) The process as set forth in claim 6 wherein F is at least about 1 kg/hr.

16. (Original) The process as set forth in claim 6 wherein F ranges from about 1.5 kg/hr to about 65 kg/hr.

17. (Original) The process as set forth in claim 6 wherein F ranges from about 5 kg/hr to about 30 kg/hr.

18. (Original) The process as set forth in claim 6 wherein F ranges from about 10 kg/hr to about 20 kg/hr.

19. (Original) The process as set forth in claim 6 wherein f is at least about 1 g/s.

20. (Original) The process as set forth in claim 6 wherein f ranges from about 5 g/s to about 35 g/s.

21. (Original) The process as set forth in claim 6 wherein f ranges from about 10 g/s to about 25 g/s.

22. (Original) The process as set forth in claim 6 wherein t_{on} is at least about 1 second.

23. (Original) The process as set forth in claim 6 wherein t_{on} ranges from about 2 seconds to about 10 seconds.

24. (Original) The process as set forth in claim 6 wherein t_{on} ranges from about 4 seconds to about 10 seconds.

25. (Original) The process as set forth in claim 6 wherein t_{on} is about 5 seconds.

26. (Original) The process as set forth in claim 6 wherein t_{off} is at least about 1 second.

27. (Original) The process as set forth in claim 6 wherein t_{off} is at least about 5 seconds.

28. (Original) The process as set forth in claim 6 wherein t_{off} ranges from about 10 seconds to about 30 seconds.

29. (Original) The process as set forth in claim 6 wherein t_{off} ranges from about 10 seconds to about 20 seconds.

30. (Original) The process as set forth in claim 6 wherein t_{off} ranges from about 10 seconds to about 15 seconds.

31. (Original) The process as set forth in claim 6 wherein t_{off} is about 12 seconds.

32. (Original) The process as set forth in claim 6 wherein the flow of the granular polycrystalline silicon is interrupted during the off-period using an angle of repose valve.

33. (Original) The process as set forth in claim 6 wherein the feed device directs the granular polycrystalline silicon onto a portion of the exposed unmelted polycrystalline.

34. (Original) The process as set forth in claim 33 wherein the feed device through which the granular polycrystalline silicon is flowed is a vertical-type feed tube that is positioned so that it is not directly above the center of the exposed unmelted polycrystalline silicon.

35. (Original) The process as set forth in claim 33 wherein the feed device through which the granular polycrystalline silicon is flowed is a spray-type feed tube.

36. (Original) The process as set forth in claim 33 wherein the portion of the exposed unmelted polycrystalline upon which the granular polycrystalline silicon is delivered is a wedge that extends radially outward from about the center to the interface between the unmelted polycrystalline silicon and the upper surface of the molten silicon.

37. (Original) The process as set forth in claim 36 wherein the wedge has a wedge angle that is about 180°.

38. (Original) The process as set forth in claim 33 wherein the wedge has a wedge angle that is less than about 180°.

39. (Original) The process as set forth in claim 33 wherein the wedge has a wedge angle that is about 120°.

40. (Original) The process as set forth in claim 33 wherein the wedge has a wedge angle that is less than about 120°.

41. (Original) The process as set forth in claim 33 wherein the wedge has a wedge angle that is about 90°.

42. (Original) The process as set forth in claim 33 wherein the wedge has a wedge angle that is less than about 90°.

43. (Original) The process as set forth in claim 33 wherein the wedge has a wedge angle that ranges from about 40° to about 72°.

44. (Original) The process as set forth in claim 33 wherein the wedge has a wedge angle that is about 72°.

45. (Original) The process as set forth in claim 33 wherein the wedge has a wedge angle that is about 60°.

46. (Original) The process as set forth in claim 33 wherein the wedge has a wedge angle that is about 51.4°.

47. (Original) The process as set forth in claim 33 wherein the wedge has a wedge angle that is about 45°.

48. (Original) The process as set forth in claim 33 wherein the wedge has a wedge angle that is about 40°.

49. (Original) The process as set forth in claim 33 wherein the wedge has a wedge angle that is about 36°.

50. (Original) The process as set forth in claim 33 wherein the wedge has a wedge angle that is about 30°.

51. (Original) The process as set forth in claim 33 wherein the wedge has a wedge angle that is about 27.7°.

52. (Original) The process as set forth in claim 33 wherein each wedge on the exposed unmelted polycrystalline silicon does not substantially overlap with the immediately preceding wedge.

53. (Original) The process as set forth in claim 52 wherein granular polycrystalline silicon is deposited on the entire exposed unmelted polycrystalline silicon prior to redepositing granular polycrystalline silicon on any wedge.

54. (Original) The process as set forth in claim 53 wherein each subsequent wedge is deposited adjacent to the immediately preceding wedge and within one rotation of the crucible after the immediately preceding wedge.

55. (Original) The process as set forth in claim 53 wherein each subsequent wedge is deposited adjacent to the immediately preceding wedge and following at least one rotation of the crucible after the immediately preceding wedge.

56. (Original) The process as set forth in claim 53 wherein each subsequent wedge is deposited nearly opposite from the immediately preceding wedge, and adjacent to the second-most recent wedge and within one rotation of the crucible after the second-most recent wedge.

57. (Original) The process as set forth in claim 53 wherein each subsequent wedge is deposited nearly opposite from the

immediately preceding wedge, and adjacent to the second-most recent wedge and following at least one rotation of the crucible after the second-most recent wedge.

58. (Original) The process as set forth in claim 52 wherein granular polycrystalline silicon is redeposited on a wedge prior to the depositing granular polycrystalline silicon on the entire exposed unmelted polycrystalline silicon.

59. (Currently amended) A process for preparing a silicon melt in a crucible from which a single crystal silicon ingot is grown from polycrystalline silicon for use in growing the single crystal silicon ingot by the Czochralski method, the process comprising:

a. loading the crucible with chunk polycrystalline silicon, the amount of the chunk polycrystalline silicon load being between about 40% to about 65% by weight of the total amount of the polycrystalline silicon melted to form the silicon melt;

b. rotating the loaded crucible from which the single crystal silicon ingot is grown;

c. heating the loaded chunk polycrystalline silicon to form molten silicon and unmelted polycrystalline silicon, the molten silicon comprising an upper surface, the unmelted polycrystalline silicon comprising an exposed portion that is above the upper surface of the molten silicon, the exposed unmelted polycrystalline having a center and a width that corresponds to the longest distance between two points along the interface between the exposed unmelted polycrystalline silicon and the upper surface of the molten silicon, the interface between the unmelted polycrystalline silicon and the upper surface of the molten silicon being approximately equidistant from the center of the unmelted polycrystalline silicon;

d. feeding additional granular polycrystalline silicon into the rotating crucible by intermittently delivering the additional granular polycrystalline silicon out of a feed tube in the crucible and onto the exposed portion of the unmelted polycrystalline silicon of said partially melted charge in the crucible from which the single crystal silicon ingot is grown thereby maintaining the width of the exposed unmelted polycrystalline silicon, the intermittent delivery comprising a plurality of alternating on-periods and off-periods, wherein each on-period comprises flowing the additional granular polycrystalline silicon through a feed device that directs the additional granular polycrystalline silicon onto a wedge of the exposed unmelted polycrystalline silicon that does not substantially overlap with the immediately preceding wedge, and wherein each off-period comprises interrupting the flow of the additional granular polycrystalline silicon through the feed device; and

d. melting the loaded polycrystalline silicon and the additional granular polycrystalline silicon to form the silicon melt in the crucible from which the single crystal silicon ingot is grown.

60. (Currently amended) A process for preparing a silicon melt in a crucible from which a single crystal silicon ingot is grown from polycrystalline silicon for use in growing the single crystal silicon ingot by the Czochralski method, the process comprising:

a. loading the crucible with chunk polycrystalline silicon, the amount of the chunk polycrystalline silicon load being between about 40% to about 65% by weight of the total amount of the polycrystalline silicon melted to form the silicon melt, the crucible comprising an interior wall and having an inner diameter, D ;

b. rotating the loaded crucible from which the single crystal silicon ingot is grown at a rate, r , that ranges from about 1 rpm to about 5 rpm;

c. heating the loaded chunk polycrystalline silicon to form molten silicon and unmelted polycrystalline silicon, the molten silicon comprising an upper surface, the unmelted polycrystalline silicon comprising an exposed portion that is above the upper surface of the molten silicon, the exposed unmelted polycrystalline having a center and a width, d , that corresponds to the longest distance between two points along the interface between the exposed unmelted polycrystalline silicon and the upper surface of the molten silicon, the interface between the unmelted polycrystalline silicon and the upper surface of the molten silicon being approximately equidistant from the center of the unmelted polycrystalline silicon and approximately equidistance from the interior wall of the crucible;

d. feeding additional granular polycrystalline silicon into the rotating crucible by intermittently delivering the additional granular polycrystalline silicon out of a feed tube in the crucible and onto the exposed portion of the unmelted polycrystalline silicon of said partially melted charge in the crucible from which the single crystal silicon ingot is grown thereby maintaining the width of the exposed unmelted polycrystalline silicon, d , at about 65% to about 85% of the crucible diameter, D , the intermittent delivery comprising a plurality of alternating on-periods and off-periods, wherein each on-period comprises flowing the additional granular polycrystalline silicon at a flow rate, f , of about 5 g/s to about 35 g/s for duration, t_{on} , of about 2 seconds to about 10 seconds through a feed device that directs the additional granular polycrystalline silicon onto a wedge of the exposed unmelted polycrystalline silicon wherein each wedge has a wedge

angle of about 40° to about 72° and each wedge does not substantially overlap with the immediately preceding wedge, and wherein each off-period comprises interrupting the flow of the additional granular polycrystalline silicon through the feed device for a duration, t_{off} , of at least about 5 seconds; and

d. melting the loaded polycrystalline silicon and the additional granular polycrystalline silicon to form the silicon melt in the crucible from which the single crystal silicon ingot is grown.

61. (Original) The process as set forth in claim 60 wherein d is about 75% of D , r ranges from about 2 rpm to about 3 rpm, f ranges from about 10 g/s to 25 g/s, t_{on} ranges from about 4 seconds to about 10 seconds, and t_{off} ranges from about 10 seconds to about 30 seconds.

62. (Original) The process as set forth in claim 60 wherein granular polycrystalline silicon is deposited on the entire exposed unmelted polycrystalline silicon prior to redepositing granular polycrystalline on any wedge.

63. (Original) The process as set forth in claim 62 wherein each subsequent wedge is deposited adjacent to the immediately preceding wedge and within one rotation of the crucible after the immediately preceding wedge.

64. (Original) The process as set forth in claim 62 wherein each subsequent wedge is deposited adjacent to the immediately preceding wedge and following at least one rotation of the crucible after the immediately preceding wedge.

65. (Original) The process as set forth in claim 62 wherein each subsequent wedge is deposited nearly opposite from the

immediately preceding wedge, and adjacent to the second-most recent wedge and within one rotation of the crucible after the second-most recent wedge.

66. (Original) The process as set forth in claim 62 wherein each subsequent wedge is deposited nearly opposite from the immediately preceding wedge, and adjacent to the second-most recent wedge and following at least one rotation of the crucible after the second-most recent wedge.

67. (Previously presented) The process as set forth in claim 60 wherein the additional granular polycrystalline silicon is redeposited on a wedge prior to the depositing the additional granular polycrystalline silicon on the entire exposed unmelted polycrystalline silicon.

68. (Currently amended) A process for preparing a silicon melt in a crucible from which a single crystal silicon ingot is grown for use in growing the single crystal silicon ingot by the Czochralski method, the process comprising:

- a. rotating the crucible at a rate, r ;
- b. forming a depleted molten silicon charge in the rotating crucible from which the single crystal silicon ingot is grown, the depleted molten silicon charge having a weight, w , the crucible comprising an interior wall and having an inner diameter, D ;
- c. feeding polycrystalline silicon into the rotating crucible by delivering the polycrystalline silicon onto the depleted molten silicon charge to form a partial charge comprising molten silicon and unmelted polycrystalline silicon, the molten silicon comprising an upper surface, the unmelted polycrystalline silicon comprising an exposed portion that is above the surface of the molten silicon, the exposed unmelted

polycrystalline silicon having a center and width, d , that corresponds to the longest distance between two points along the interface between the exposed unmelted polycrystalline silicon and upper surface of the molten silicon;

d. feeding additional polycrystalline into the rotating crucible by intermittently delivering the additional polycrystalline silicon out of a feed tube in the crucible and onto the exposed of said partially melted charge portion of the unmelted polycrystalline silicon in the crucible from which the single crystal silicon ingot is grown thereby maintaining the width of the exposed unmelted polycrystalline silicon, d , the intermittent delivery comprising a plurality of alternating on-periods and off-periods, wherein each on-period comprises flowing the additional polycrystalline silicon at a flow rate, f , for a duration, t_{on} , through a feed device that directs the additional polycrystalline silicon onto the exposed unmelted polycrystalline silicon, and wherein each off-period comprises interrupting the flow of the additional polycrystalline silicon through the feed device for a duration, t_{off} ; and

e. melting the unmelted polycrystalline silicon and the additional polycrystalline silicon to form the silicon melt in the crucible from which the single crystal silicon ingot is grown.

69. (Original) The process as set forth in claim 68 wherein w is about 15% to about 40% by weight of the silicon melt.

70. (Original) The process as set forth in claim 68 wherein w is about 20% to about 30% by weight of the silicon melt.

71. (Original) The process as set forth in claim 68 wherein the interface between the unmelted polycrystalline silicon and the upper surface of the molten silicon is approximately

equidistant from the center of the unmelted polycrystalline silicon and approximately equidistant from the interior wall of the crucible.

72. (Previously presented) The process as set forth in claim 71 wherein the polycrystalline silicon and the additional polycrystalline silicon fed into the crucible are granular polycrystalline silicon.

73. (Original) The process as set forth in claim 72 wherein d ranges from about 65% to about 85% of D .

74. (Original) The process as set forth in claim 72 wherein d is about 75% of D .

75. (Original) The process as set forth in claim 73 wherein r ranges from about 1 rpm to about 5 rpm.

76. (Original) The process as set forth in claim 73 wherein r ranges from about 2 rpm to about 3 rpm.

77. (Original) The process as set forth in claim 75 wherein f ranges from about 5 g/s to about 35 g/s.

78. (Original) The process as set forth in claim 75 wherein f ranges from about 10 g/s to about 25 g/s.

79. (Original) The process as set forth in claim 77 wherein t_{on} ranges from about 2 seconds to about 10 seconds.

80. (Original) The process as set forth in claim 77 wherein t_{on} ranges from about 4 seconds to about 10 seconds.

81. (Original) The process as set forth in claim 79 wherein t_{off} is at least about 5 seconds.

82. (Original) The process as set forth in claim 79 wherein t_{off} ranges from about 10 seconds to about 30 seconds.

83. (Original) The process as set forth in claim 79 wherein t_{off} ranges from about 10 seconds to about 20 seconds.

84. (Original) The process as set forth in claim 79 wherein t_{off} ranges from about 10 seconds to about 15 seconds.

85. (Original) The process as set forth in claim 81 wherein the feed device directs the granular polycrystalline silicon onto a portion of the exposed unmelted polycrystalline.

86. (Original) The process as set forth in claim 85 wherein the portion of the exposed unmelted polycrystalline silicon upon which the granular polycrystalline silicon is delivered is a wedge that extends radially outward from about the center to the interface between the unmelted polycrystalline silicon and the upper surface of the molten silicon.

87. (Original) The process as set forth in claim 86 wherein the wedge has a wedge angle that is less than about 180°.

88. (Original) The process as set forth in claim 86 wherein the wedge has a wedge angle that ranges from about 40° to about 72°.

89. (Original) The process as set forth in claim 86 wherein the wedge has a wedge angle that is about 60°, or 51.4°, or 45°, or 40°, or 36°, or 30° or 27.7°.

90. (Original) The process as set forth in claim 86 wherein each wedge on the exposed unmelted polycrystalline silicon does not substantially overlap with the immediately preceding wedge.

91. (Original) The process as set forth in claim 90 wherein granular polycrystalline silicon is deposited on the entire exposed unmelted polycrystalline silicon prior to redepositing granular polycrystalline silicon on any wedge.

92. (Original) The process as set forth in claim 91 wherein each subsequent wedge is deposited adjacent to the immediately preceding wedge and within one rotation of the crucible after the immediately preceding wedge.

93. (Original) The process as set forth in claim 91 wherein each subsequent wedge is deposited adjacent to the immediately preceding wedge and following at least one rotation of the crucible after the immediately preceding wedge.

94. (Original) The process as set forth in claim 91 wherein each subsequent wedge is deposited nearly opposite from the immediately preceding wedge, and adjacent to the second-most recent wedge and within one rotation of the crucible after the second-most recent wedge.

95. (Original) The process as set forth in claim 91 wherein each subsequent wedge is deposited nearly opposite from the immediately preceding wedge, and adjacent to the second-most recent wedge and following at least one rotation of the crucible after the second-most recent wedge.

96. (Original) The process as set forth in claim 90 wherein granular polycrystalline silicon is redeposited on a wedge prior

to the depositing granular polycrystalline silicon on the entire exposed unmelted polycrystalline silicon.

97. (Previously presented) The process as set forth in claim 1 further comprising growing a single crystal silicon ingot by the Czochralski method from the silicon melt in the crucible.

98. (Previously presented) The process as set forth in claim 2 further comprising growing a single crystal silicon ingot by the Czochralski method from the silicon melt in the crucible.

99. (Previously presented) The process as set forth in claim 3 further comprising growing a single crystal silicon ingot by the Czochralski method from the silicon melt in the crucible.

100. (Previously presented) The process as set forth in claim 59 further comprising growing a single crystal silicon ingot by the Czochralski method from the silicon melt in the crucible.

101. (Previously presented) The process as set forth in claim 60 further comprising growing a single crystal silicon ingot by the Czochralski method from the silicon melt in the crucible.

102. (Previously presented) The process as set forth in claim 68 further comprising growing a single crystal silicon ingot by the Czochralski method from the silicon melt in the crucible.